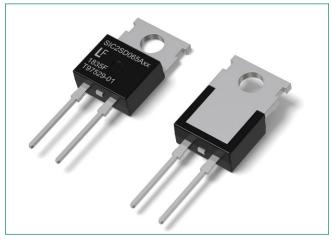


# LSIC2SD065A16A 650 V, 16 A SiC Schottky Barrier Diode





\*Image for reference only, for details refer to Dimensions-Packag.

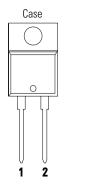
#### Description

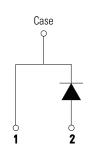
This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. These diodes series are ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

#### **Features**

- AEC-Q101 qualified
- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C maximum operating junction temperature
- Excellent surge capability
- Extremely fast, temperature-independent switching behavior
- Dramatically reduced switching losses compared to Si bipolar diodes

#### Circuit Diagram TO-220-2L





#### **Applications**

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Uninterruptible power supplies
- Solar inverters
- Industrial motor drives
- EV charging stations

### Environmental

- Littelfuse "RoHS" logo = RoHS RoHS conform
- Littelfuse "HF" logo =**HF**Halogen Free
- Littelfuse "Pb-free" logo = Pb-free lead plating



#### **Maximum Ratings**

Characteristics	Symbol	Conditions	Value	Unit	
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	-	650	V	
DC Blocking Voltage	V <sub>R</sub>	T <sub>J</sub> = 25 °C	650	V	
Continuous Forward Current		T <sub>c</sub> = 25 °C	38		
	I <sub>F</sub>	T <sub>C</sub> = 135 °C	17.2	А	
		T <sub>C</sub> = 140 °C	16		
Non-Repetitive Forward Surge Current	I <sub>FSM</sub>	$T_{\rm C}$ = 25 °C, $T_{\rm P}$ = 10 ms, Half sine pulse	70	А	
Power Dissipation	D	T <sub>C</sub> = 25 °C	$T_{c} = 25  ^{\circ}\text{C}$ 125		
	P <sub>Tot</sub>	T <sub>C</sub> = 110 °C	54	W	
Operating Junction Temperature	T	-	-55 to 175	°C	
Storage Temperature	T <sub>STG</sub>	-	-55 to 150	°C	
Soldering Temperature	T <sub>SOLD</sub>	-	260	°C	

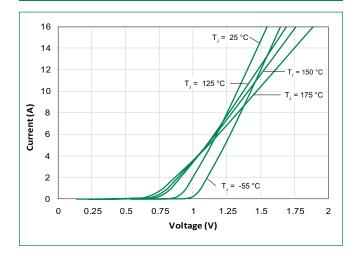


#### Electrical Characteristics (T<sub>1</sub> =25 °C unless otherwise specified)

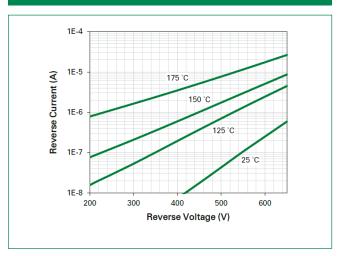
Characteristics Symb	Completed.	conditions	Value			11
	Symbol		Min.	Тур.	Max.	Unit
Forward Voltage	\/	I <sub>F</sub> = 16 A, T <sub>J</sub> = 25 °C	-	1.5	1.8	V
	V <sub>F</sub>	$V_{F}$ $I_{F} = 16 \text{ A}, T_{J} = 175 ^{\circ}\text{C}$	-	1.85	-	
Reverse Current		$V_{R} = 650 \text{ V}, T_{J} = 25 \text{ °C}$	-	<1	50	μΑ
	I <sub>R</sub>	V <sub>R</sub> = 650 V, T <sub>J</sub> = 175 °C	-	55	-	
Total Capacitance		V <sub>R</sub> = 1 V, f = 1 MHz	-	730	-	pF
	С	V <sub>R</sub> = 200 V, f = 1 MHz	-	92	-	
		V <sub>R</sub> = 400 V, f = 1 MHz - 66	-			
Total Capacitive Charge	Q <sub>c</sub>	$V_R = 400 \text{ V}, \ Q_c = \int_{C}^{V_R} C(V) dV$	-	48	-	nC

Thermal Characteristics					
Characteristics	Symbol	Value	Unit		
Thermal Resistance	В	1.2	°C/W		

#### **Figure 1: Typical Foward Characteristics**



## **Figure 2: Typical Reverse Characteristics**





**Figure 3: Power Derating** 

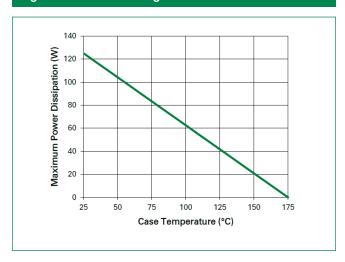


Figure 4: Current Derating

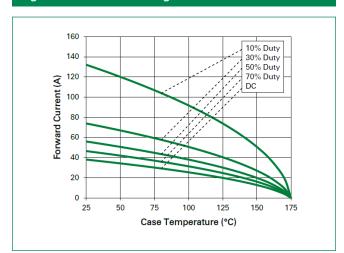


Figure 5: Capacitance vs. Reverse Voltage

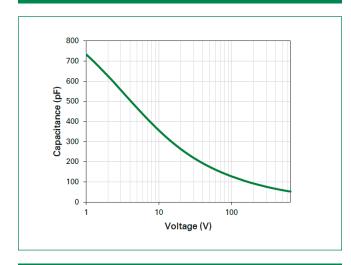


Figure 6: Capacitive Charge vs. Reverse Voltage

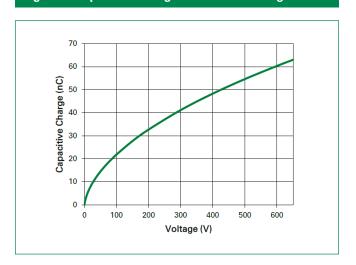


Figure 7: Stored Energy vs. Reverse Voltage

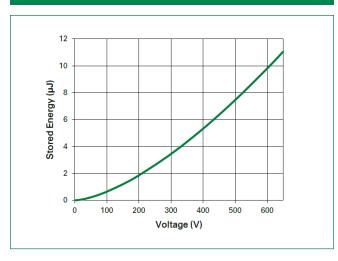
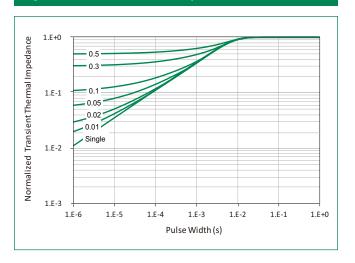
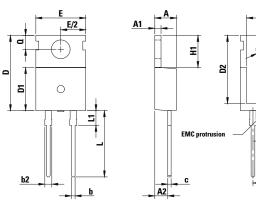


Figure 8: Transient Thermal Impedance

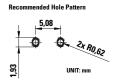




## Dimensions-Package TO-220-2L

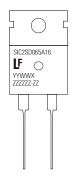


A1 A	1H 20	E1 - P
A2	EMC protrusion —	e1



Complete	Millimeters				
Symbol	Min	Nom	Max		
Α	4.30	4.45	4.70		
A1	1.14	1.27	1.40		
A2	2.20	-	2.74		
b	0.69	-	0.90		
b2	1.17	-	1.62		
С	0.36	-	0.60		
D	14.90	-	15.90		
D1	8.62	-	9.40		
D2	12.50	-	12.95		
E	9.70	10.18	10.36		
E1	7.57	7.61	8.30		
e1	-	2.54	-		
е	5.03	5.08	5.13		
H1	6.30	6.55	6.80		
L	12.88	13.50	14.00		
L1	2.39	-	3.25		
øΡ	3.50	3.84	3.96		
Q	2.65	-	3.05		
R	-	-	0.25		

#### **Part Numbering and Marking System**



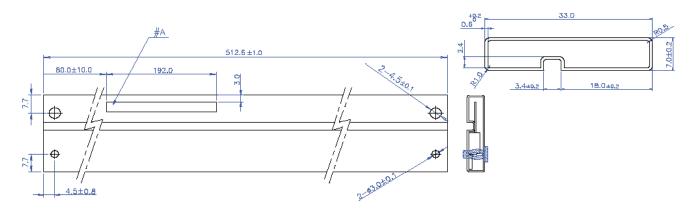
SIC	= SiC Diode			
2	= Gen2			
SD	= Schottky Diode			
065	= Voltage Rating (650 V)			
Α	= TO-220 Package (2 Lead)			
16	= Current Rating (16 A)			
YY	= Year			
WW	= Week			
Χ	= Special Code			
ZZZZZZ-ZZ = Lot Number				

### **Packing Options**

Part Number	Marking	Packing Mode	D.O.M
LSIC2SD065A16A	SIC2SD065A16	Tube(50pcs)	1000

## **GEN2 SiC Schottky Diode** LSIC2SD065A16A, 650V, 16A, TO-220-2L

## Packing Specification (Tube for TO-220-2L)



#### [ NOTE ]

- 1. TUBE MATERIAL : PVC / PET (WITH ANTISTATIC COATING)
  - COLOR : TRANSPARENCY, RED, YELLO
  - MARKING #A : BLACK COLOR, LETTER STYLE : Arial
  - Tube Surface Resistance  $:\!10^6\!\!\sim\!10^{11}\,\Omega\,/square$
  - ESD (Electro Static Discharge) : less than 100 [volts], 6 Months
  - CAMBAR : 1.5 MAX
- 2. PIN COLOR : GREEN (ONE PIN MUST BE INSERTED IN LEFT-SIDE OF "ANTISTATIC" AND ANOTHER PIN IS FREE.)

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SS3003CH-TL-E GA01SHT18 CRS10I30A(TE85L,QM MA4E2501L-1290 MBRB30H30CT-1G SB007-03C-TB-E SK32A-TP SK33B-TP
SK38B-TP NRVBM120LT1G NTE505 NTSB30U100CT-1G SS15E-TP VS-6CWQ10FNHM3 ACDBA1100LR-HF ACDBA1200-HF
ACDBA140-HF ACDBA2100-HF ACDBA3100-HF CDBQC0530L-HF CDBQC0240LR-HF ACDBA260LR-HF ACDBA1100-HF
SK310B-TP MA4E2502L-1246 MA4E2502H-1246 NRVBM120ET1G NSR01L30MXT5G NTE573 NTE6081 SB560 PMAD1108-LF
SD103ATW-TP